

EAST Search History**EAST Search History (Prior Art)**

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	21	(US-20060240602-\$ or US-20060166415-\$ or US-20060049428-\$ or US-20030054586-\$ or US-20070020826-\$ or US-20050116231-\$ or US-20030189208-\$).did. or (US-5686349-\$ or US-6017779-\$ or US-6078059-\$ or US-6093660-\$ or US-7439191-\$ or US-6756324-\$ or US-6329270-\$ or US-6271062-\$ or US-5796116-\$ or US-6188452-\$ or US-5962896-\$ or US-5576229-\$ or US-5403756-\$). did. or (EP-1445802-\$).did.	US-PGPUB; USPAT; EPO	OR	ON	2010/08/26 12:28
L2	1	("5480818").PN.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2010/08/26 13:48
L3	18	1 and (mobilit\$4)	US-PGPUB; USPAT; EPO	OR	ON	2010/08/26 15:09
L4	13	1 and (mobilit\$4) and (microcrystal\$5 or ".mu.c-Si")	US-PGPUB; USPAT; EPO	OR	ON	2010/08/26 15:10
L5	3	1 and ((mobilit\$4) with ("cm.sup.2 /Vs" or "Vs")) and (microcrystal\$5 or ".mu.c-Si")	US-PGPUB; USPAT; EPO	OR	ON	2010/08/26 15:13
L6	78	(ROCA near3 CABARROCAS).in. or VANDERHAGHEN-REGIS.in. or DREVILLON-BERNARD.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; BM_TDB	OR	ON	2010/08/26 15:16
L7	0	6 and ((mobilit\$4) with ("cm.sup.2 /Vs" or "Vs")) and (microcrystal\$5 or ".mu.c-Si")	US-PGPUB; USPAT; EPO	OR	ON	2010/08/26 15:16
L8	2	6 and ((mobilit\$4) with ("cm.sup.2 /Vs" or "Vs"))	US-PGPUB; USPAT; EPO	OR	ON	2010/08/26 15:16
L9	3	6 and ((mobilit\$4) with ("cm.sup.2/Vs" or "Vs" or "cm.sup.2"))	US-PGPUB; USPAT; EPO	OR	ON	2010/08/26 15:17
L10	8	1 and ((mobilit\$4) with ("cm.sup.2/Vs" or "Vs" or "cm.sup.2"))	US-PGPUB; USPAT; EPO	OR	ON	2010/08/26 15:17

L11	15344	((438/29,30,69,82,99,149,151,161,485,676,680) or (257/E29.292, E29.293,E29.294)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2010/08/26 15:22
L12	6400	L11 and @ad<"20030206"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2010/08/26 15:22
L13	242	12 and ((mobilit\$4) with ("cm.sup.2/Vs" or "Vs" or "cm.sup.2")) and (microcrystal\$5 or ".mu.c-Si")	US-PGPUB; USPAT; EPO	OR	ON	2010/08/26 15:22
L14	30	12 and ((mobilit\$4) with ("cm.sup.2/Vs" or "Vs" or "cm.sup.2")) same (microcrystal\$5 or ".mu.c-Si")	US-PGPUB; USPAT; EPO	OR	ON	2010/08/26 15:25
L15	65	("438".clas. or "257".clas.) and @ad<"20040206" and ((mobilit\$4) with ("cm.sup.2/Vs" or "Vs" or "cm.sup.2")) same (microcrystal\$5 or ".mu.c-Si")	US-PGPUB; USPAT; EPO	OR	ON	2010/08/26 16:07
L16	10	("438".clas. or "257".clas.) and @ad<"20040206" and ((mobilit\$4) with ("cm.sup.2/Vs" or "Vs" or "cm.sup.2")) with (microcrystal\$5 or ".mu.c-Si")	US-PGPUB; USPAT; EPO	OR	ON	2010/08/26 16:20
L17	8846	L11 and @ad>"20030206"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2010/08/26 17:49
L18	8847	L11 and @ad>"20030205"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2010/08/26 17:50
L19	5	18 and (microcrystal\$5 same transistor\$4).clm. and (plasma with (insulat\$4 or dielectr\$4)).clm. and grain\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2010/08/26 17:50

L20	10	18 and ((microcrystal\$5 or ".mu.c-Si") same transistor\$4).clm. and ((mobilit\$4) with ("cm.sup.2/Vs" or "Vs" or "cm.sup.2"))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2010/08/26 17:52
S1	1	("20060240602").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2009/03/23 14:25
S3	67	(ROCA near3 CABARROCAS).in. or VANDERHAGHEN-REGI S.in. or DREVILLON-BERNARD.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/03/23 14:27
S4	2	S3 and (transistor).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/03/23 14:28
S5	3	("5686349" "6017779" "6078059").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/03/23 14:30
S6	44	(257/E31.045).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2009/03/23 15:30
S7	413	(257/E29.294).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2009/03/23 15:32

S8	1502	(257/E29.293).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2009/03/23 15:32
S9	134	(257/E29.292).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2009/03/23 15:32
S10	1855	(257/E29.292,E29.293,E29.294).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2009/03/23 15:37
S11	966	S10 and @ad<"20030206"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/03/23 15:37
S12	44	S11 and ((grain with size) same (microcrystalline or (micro adj crystalline)))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/03/23 15:38
S15	12651	((438/29,30,69,82,99,149,151,161,485,676,680) or (257/E29.292, E29.293,E29.294)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2009/03/23 15:48
S16	6382	S15 and @ad<"20030206"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/03/23 15:48

S17	26	S16 and (top adj gate).ab. and ((PECVD or plasma) same (silicon or microcrystalline or ".mu.c-Si"))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/03/23 16:05
S18	432	S16 and (top adj gate) and ((PECVD or plasma) same (silicon or microcrystalline or ".mu.c-Si"))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/03/23 16:09
S19	61	S16 and (top adj gate) and ((PECVD or plasma) same (microcrystalline or ".mu.c-Si"))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/03/23 16:09
S20	60	S19 not S17	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/03/23 16:09
S21	8	S11 and (crystalline near3 fraction)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/03/23 17:14
S22	13	S16 and (crystalline near3 fraction) and transistor and (microcrystalline or ".mu.c\$4")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/03/23 17:19
S23	35	@ad<"20030206" and (crystalline near3 fraction) and transistor and (microcrystalline or ".mu.c\$4")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/03/23 17:20

S24	22	S23 not S22	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/03/23 17:20
S25	12664	((438/29,30,69,82,99,149,151,161,485,676,680) or (257/E29.292, E29.293,E29.294)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2009/03/24 13:37
S26	6382	S25 and @ad<"20030206"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/03/24 13:37
S27	28	S26 and ((plasma with treat\$4 with (gate adj insulat\$4)))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/03/24 13:38
S28	8	TFT and @ad<"20030206" and ((plasma with treat\$4 with (gate adj insulat\$4)) same ("o.sub.2"))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/03/24 14:02
S29	1502	(257/E29.293).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2009/03/24 14:43
S30	167	S29 and ((top adj gate) same (bottom adj gate))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/03/24 14:44

S33	199	"438".clas. and @ad<"20030206" and ((plasma with treat\$4 with (insulat\$4) same (improv\$4 or reduc\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/03/24 16:00
S34	160	"438".clas. and @ad<"20030206" and ((plasma with treat\$4 with (insulat\$4) same (improv\$4 or reduc\$4))	US-PGPUB; USPAT	OR	ON	2009/03/24 16:00
S35	13	"438".clas. and @ad<"20030206" and ((plasma with treat\$4 with (insulat\$4) with ("n.sub.2" or "o.sub.2")) same (improv\$4 or reduc\$4))	US-PGPUB; USPAT	OR	ON	2009/03/24 16:01
S36	17	("438".clas. or "257".clas.) and @ad<"20030206" and ((plasma with treat\$4 with (insulat\$4) with ("n.sub.2" or "o.sub.2")) same (improv\$4 or reduc\$4))	US-PGPUB; USPAT	OR	ON	2009/03/24 16:56
S37	90	("438".clas. or "257".clas.) and @ad<"20030206" and (plasma with treat\$4 with (insulat\$4) with ("n.sub.2" or "o.sub.2"))	US-PGPUB; USPAT	OR	ON	2009/03/24 16:57
S38	67	(ROCA near3 CABARROCAS).in. or VANDERHAGHEN-REGIS.in. or DREVILLON-BERNARD.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/11/23 11:47
S39	4	S38 and (microcrystal\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/11/23 11:48
S40	1	("438".clas. or "257".clas.) and @ad<"20030206" and ((microcrystal\$5) same (fraction\$3 with "%"))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/11/23 11:52
S41	3	("438".clas. or "257".clas.) and @ad<"20030206" and ((microcrystal\$5) and (fraction\$3 with "%"))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/11/23 11:52

S42	24	("438".clas. or "257".clas.) and @ad<"20030206" and ((microcrystal\$5) and (fraction\$3 same "%"))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/11/23 11:53
S45	387	("438".clas. or "257".clas.) and @ad<"20030206" and (microcrystal\$5 same transistor\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/11/23 11:56
S46	300	("438".clas. or "257".clas.) and @ad<"20030206" and (microcrystal\$5 same transistor\$4) and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/11/23 11:56
S47	157	("438".clas. or "257".clas.) and @ad<"20030206" and (microcrystal\$5 same transistor\$4) and plasma and grain\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/11/23 11:57
S48	92	("438".clas. or "257".clas.) and @ad<"20030206" and (microcrystal\$5 same transistor\$4) and (plasma with (insulat\$4 or dielectr\$4)) and grain\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2009/11/23 11:59
S49	2	(("6017779") or ("6078059")).PN.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2009/11/23 14:36
S50	1	("20030189208").PN.	US-PGPUB; USPAT; EPO; JPO	OR	OFF	2009/11/23 15:29
S51	75	(ROCA near3 CABARROCAS).in. or VANDERHAGHEN-REGIS.in. or DREVILLON-BERNARD.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2010/03/30 12:52

S52	2	S51 and (transistor\$2).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2010/03/30 12:53
S53	2	S51 and (display\$2).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2010/03/30 13:10
S54	21	(US-20060240602-\$ or US-20060166415-\$ or US-20060049428-\$ or US-20030054586-\$ or US-20070020826-\$ or US-20050116231-\$ or US-20030189208-\$).did. or (US-5686349-\$ or US-6017779-\$ or US-6078059-\$ or US-6093660-\$ or US-7439191-\$ or US-6756324-\$ or US-6329270-\$ or US-6271062-\$ or US-5796116-\$ or US-6188452-\$ or US-5962896-\$ or US-5576229-\$ or US-5403756-\$).did. or (EP-1445802-\$).did.	US-PGPUB; USPAT; EPO	OR	ON	2010/03/30 13:10

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